TECHNICAL DATA DATA SHEET 4682, REV. A

HERMETIC POWER SCHOTTKY RECTIFIER Low Forward Voltage

Applications:

• Switching Power Supply • Converters • Free-Wheeling Diodes • Polarity Protection Diode

Features:

- Soft Reverse Recovery at Low and High Temperature
- Low Forward Voltage Drop
- Low Power Loss, High Efficiency
- High Surge Capacity
- Guard Ring for Enhanced Durability and Long Term Reliability
- Guaranteed Reverse Avalanche Characteristics

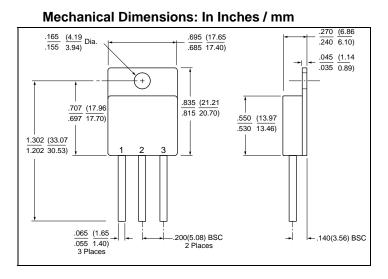
Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Inverse Voltage	V _{RWM}	-	100	V
Max. Average Forward Current	I _{F(AV)}	50% duty cycle, rectangular wave form (Single/Doubler)	15	A
Max. Average Forward Current	I _{F(AV)}	50% duty cycle, rectangular wave form (Common Cathode/Common Anode)	30	A
Max. Peak One Cycle Non- Repetitive Surge Current	I _{FSM}	8.3 ms, half Sine wave (per leg)	200	A
Max. Thermal Resistance	$R_{ ext{ heta}JC}$	(Single)	1.45	°C/W
Max. Thermal Resistance	$R_{ ext{ heta}JC}$	(Common Cathode/Common Anode/Doubler) (per leg)	0.72	°C/W
Max. Junction Temperature	ΤJ	-	-65 to +200	°C
Max. Storage Temperature	T _{stg}	-	-65 to +200	°C

Electrical Characteristics:

Characteristics	Symbol	Condition	Max.	Units
Max. Forward Voltage Drop	V _{F1}	@ 15A, Pulse, T _J = 25 °C	0.93	V
		(per leg)		
	V _{F2}	@ 15A, Pulse, T _J = 125 °C	0.77	V
		(per leg)		
Max. Reverse Current	I _{R1}	@V _R = 100V, Pulse,	0.1	μA
		$T_J = 25 \ ^{\circ}C \ (per \ leg)$		
	I _{R2}	@V _R = 100V, Pulse,	1	mA
		T _J = 125 °C (per leg)		
Max. Junction Capacitance	CT	@V _R = 5V, T _C = 25 °C	500	pF
		f _{SIG} = 1MHz,		
		$V_{SIG} = 50 \text{mV} (\text{p-p}) (\text{per leg})$		

SENSITRON TECHNICAL DATA DATA SHEET 4682, REV. A

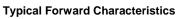


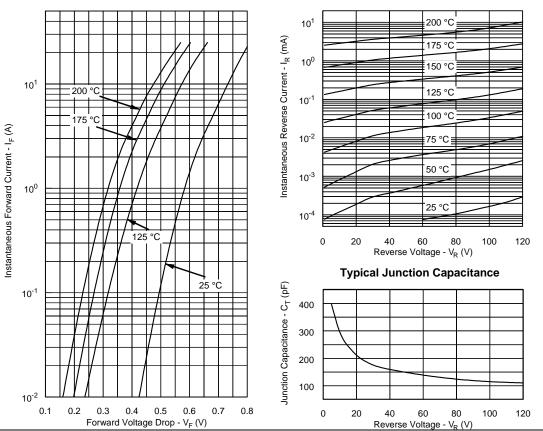
TO-258

PINOUT TABLE

ТҮРЕ	PIN 1	PIN 2	PIN 3
SINGLE RECTIFIER	CATHODE	ANODE	ANODE
DUAL RECTIFIER, COMMON CATHODE (P)	ANODE 1	COMMON CATHODE	ANODE 2
DUAL RECTIFIER, COMMON ANODE (N)	CATHODE 1	COMMON ANODE	CATHODE 2
DUAL RECTIFIER, DOUBLER (D)	ANODE	CATHODE/ANODE	CATHODE

Note: The V_f curves shown are for the unpackaged die only.







Typical Reverse Characteristics

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